

SPECIFICATION

8/22/03
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Please amend page 1, paragraph 1 as follows:

now U.S. Patent 6,344,964
This application is a divisional of U.S. Application Serial No. 09/616,951. This application is also related to Serial No. 09/298,122, "Metal-Insulator-Metal Capacitor for Copper Damascene Process and Method of Forming the Same," filed April 23, 1999, and incorporated herein by reference.

CLAIMS

- 60530-03001
1. (canceled)
 2. (canceled)
 3. (canceled)
 4. (canceled)
 5. (canceled)
 6. (canceled)
 7. (canceled)
 8. (canceled)

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- 1 9. (amended) A method of fabricating a capacitor structure, said method comprising:
 - 2 forming a bottom plate;
 - 3 forming a dielectric layer overlaying the bottom plate;
 - 4 forming over the dielectric layer a top plate having a smaller area than said bottom plate, said top
 - 5 plate having a perimeter;
 - 6 forming at least one insulating sidewall spacer placed against said perimeter of said top plate and
 - 7 overlaying a portion of said dielectric layer.

1 10. (unchanged) The method of Claim 9, and further comprising:

2 prior to forming said at least one insulating sidewall spacer, etching said top plate to expose said
3 dielectric at said perimeter of said top plate.

1 11. (unchanged) The method of Claim 9, wherein:

2 said method further comprises forming a conductor embedded in a substrate; and

3 forming the bottom plate comprises forming the bottom plate overlaying the conductor.

1 12. (unchanged) The method of Claim 11, wherein forming a conductor comprises forming a copper
2 damascene structure.

1 13. (unchanged) The method of Claim 11, wherein forming said bottom plate comprises forming a
2 conductive barrier layer in contact with said conductor.

1 14. (unchanged) The method of Claim 9, wherein each of said steps of forming a bottom plate and forming
2 a top plate comprises forming a metal plate.

1 15. (unchanged) The method of Claim 9, wherein forming the dielectric layer comprises forming a silicon
2 dioxide layer.

1 16. (unchanged) The method of Claim 9, and further comprising forming an insulating cap overlaying said
2 top plate.

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1 17. (amended) The method of Claim 16, wherein said insulating cap has a perimeter coextensive with said
2 top plate, and wherein forming said at least one insulating sidewall spacer comprising forming said at least
3 one insulating sidewall spacer against said perimeter of said insulating cap.

1 18. (newly entered) The method of Claim 9, wherein forming at least one insulating sidewall spacer
2 comprises forming at least one insulating sidewall spacer on a top surface of the dielectric layer.

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1 19. (newly entered) The method of Claim 18, wherein forming at least one insulating sidewall spacer
2 comprises forming at least one insulating sidewall spacer overlaying a portion of said bottom plate.

1 20. (newly entered) The method of Claim 9, and further comprising:
2 forming a copper damascene conductor in a substrate underlying said bottom plate.